L Number	Hits	Search Text	DB	Time stamp
31	40	lateral near4 zener adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 10:23
32	51	(lateral or horizontal) near4 zener adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 10:23
-	446	("257/339").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 15:19
-	1004	("257/355").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/02 21:29
-	1672	(("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/02 21:29
-	1474	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and (@pd<20000606 or @rlad<20010609)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/02 21:31
-	21143	npn same pnp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/02 21:31
-	114	(((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and (@pd<20000606 or @rlad<20010609)) and (npn same pnp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/02 21:31
-	322	protection adj circuit.ti,ab. and vss	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 12:40
-	2	protection adj circuit.ti,ab. and vss adj power adj line and p+ and n+	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 12:41
-	314	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 12:45
-	314	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 12:46
-	197	("257/173").CCLS.	USPAT	2002/03/03 13:33
-	23	nhv.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 13:01
-	282	("257/339").CCLS.	USPAT	2002/03/03 13:34

-	280	(("257/339").CCLS.) not (("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 13:46
-	280	(("257/339").CCLS.) not (("257/173").CCLS.)	USPAT	2002/03/03 14:01
-	501	(257/355.ccls. not 257/173.ccls.) not 257/339.ccls.	USPAT	2002/03/03 15:22
-	37	(vertical near2 (npn or pnp) near2 transistor) same protect$3 same (surge or esd or electrostatic adj discharge or human adj body adj model or hbm or breakdown adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 17:16
-	76	zener adj diode and mosfet and esd adj protection	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 17:16
-	15	zener adj diode and mosfet and esd adj protection and vss	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 17:17
-	4	zener adj diode and (mos or mosfet).ti,ab. and esd adj protection and vss	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 18:02
-	4	zener adj diode and (mos or mosfet or nmosfet or nmos or pmos or pmosfet or field adj effect adj transistor).ti,ab. and (electrostatic adj discharge or esd) adj protection.ti,ab. and vss	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 19:37
-	2	(("5519242") or ("5311042")).PN.	USPAT	2002/03/03 19:38
-	0	("prevent adj latch-up.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 20:18
-	462	prevent adj latch-up.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/03 20:19
-	44	prevent adj latch-up.ti,ab.	USPAT	2002/03/03 20:19
-	13	integrated adj circuit.ti,ab. and (prevent adj latch-up).ti,ab.	USPAT	2002/03/03 20:19
-	0	09/866,782.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 20:29
-	0	"08-101176"	JPO	2002/03/05 20:36
-	17	dairitsu	JPO	2002/03/05 20:36
-	25	dairitsu	JPO; DERWENT	2002/03/05 20:37
-	317	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:38
-	446	("257/339").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:38

-	1005	("257/355").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:38
-	1675	(("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:40
-	2	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:44
-	3	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or protection).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 21:56
-	6	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or protection).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 22:00
-	36	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or protection).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 22:00
-	0	(MOS or MOSFET) near12 protect$3 near12 (each adj other)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 08:44
-	28	plurality adj2 (mos or mosfet) and (esd or electrostatic adj discharge) adj protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 08:55
-	0	mosfet adj array and esd adj protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 08:56
-	4	mosfet adj array and esd adj protection	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:00
-	2466	phosphor$3 near6 dopant near6 type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:16

-	4	Schottky adj diode same silicide adj2 (layer or film) same protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:19
-	0	Schottky adj diode same silicide adj2 (layer or film) same esd adj protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:19
-	19	Schottky adj diode same esd adj protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:46
-	4	silicide adj (layer or film) same current same decreas$3 same schottky	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:56
-	54	schottky adj diode same protection adj2 circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:58
-	2	schottky adj diode same protection adj2 circuit same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 14:58
-	50	(schottky adj diode same (silicide adj (layer or film) or salicide)) and (esd or electrostatic adj discharge or protect$3 or hbm or human adj body adj model or surge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 15:25
-	4	(schottky adj diode near12 (silicide adj (layer or film) or salicide)) and (esd or electrostatic adj discharge or protect$3 or hbm or human adj body adj model or surge).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 15:47
-	3	5166089.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 15:50
-	0	jp-406224376$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 15:50
-	2	jp-06224376$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:22
-	62	amerasekera.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:22
-	23	amerasekera.in. and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:25
-	0	((triple adj well or triple-well) same bipolar adj transistor) and third adj2 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:46

-	33	(triple adj well or triple-well) same bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:47
-	30	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:48
-	5	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:58
-	6	"5872032"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:53
-	3	5872032.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 16:53
-	1	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab. and protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:00
-	1	(protect$3 same (triple adj well or triple-well) same bipolar adj transistor) and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:04
-	52	protect$3 and ((third near2 (impurity or diffusion)) same bipolar adj transistor) and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:06
-	12	protect$3.ti,ab. and ((third near2 (impurity or diffusion)) same bipolar adj transistor) and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:07
-	317	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/06 17:48
-	760	(zener adj diode near12 (source or drain)) and (electrostatic adj discharge or surge or esd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 07:57
-	196	(zener adj diode near12 (source or drain)) and (electrostatic adj discharge or surge or esd).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 07:58
-	157	(zener adj diode near6 (source or drain)) and (electrostatic adj discharge or surge or esd).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 08:02
-	12	(zener adj diode near6 (source or drain)) and (electrostatic adj discharge or surge or esd) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or dmos or dmosfet or ldmos or ldmosfet) and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 08:09

-	0	(lateral adj zener adj diode near6 (source or drain)) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 08:09
-	0	(lateral adj zener adj diode near6 (source or drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 08:10
-	13	lateral adj zener adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 10:18
-	0	57190357.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 09:23
-	0	57190357.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 09:23
-	0	57190357.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/07 09:23
-	1	"5023521".PN.	USPAT	2002/03/07 09:24